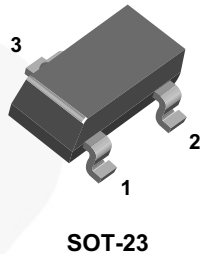


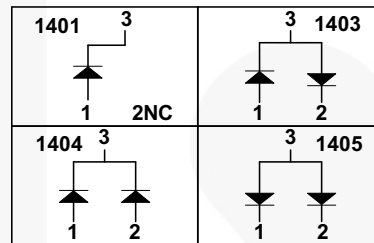


November 2014

MMBD1401 / MMBD1403 / MMBD1404 / MMBD1405 Small Signal Diodes



Connection Diagrams



Ordering Information

Part Number	Top Mark	Package	Packing Method
MMBD1401	29	SOT-23 3L	Tape and Reel
MMBD1403	32	SOT-23 3L	Tape and Reel
MMBD1404	33	SOT-23 3L	Tape and Reel
MMBD1405	34	SOT-23 3L	Tape and Reel

Absolute Maximum Ratings^{(1), (2)}

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage	200	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
I_{FSM}	Non-Repetitive Peak Forward Surge Current	Pulse Width = 1.0 second	1.0
		Pulse Width = 1.0 microsecond	2.0
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_J	Operating Junction Temperature	150	$^\circ\text{C}$

Notes:

1. These ratings are based on a maximum junction temperature of 150°C .
2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

MMBD1401 / MMBD1403 / MMBD1404 / MMBD1405 — Small Signal Diodes

Thermal Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ\text{C}/\text{W}$

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
B_V	Breakdown Voltage	$I_R = 100 \mu\text{A}$	200		V
V_F	Forward Voltage	$I_F = 10 \text{ mA}$		800	mV
		$I_F = 50 \text{ mA}$	760	920	mV
		$I_F = 200 \text{ mA}$		1.0	V
		$I_F = 300 \text{ mA}$		1.1	V
I_R	Reverse Current	$V_R = 120 \text{ V}$		40	nA
		$V_R = 175 \text{ V}$		100	nA
C_T	Total Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		2.0	pF
t_{rr}	Reverse Recovery Time	$I_F = I_R = 30 \text{ mA}, I_{RR} = 3.0 \text{ mA}, R_L = 100 \Omega$		50	nS

Typical Performance Characteristics

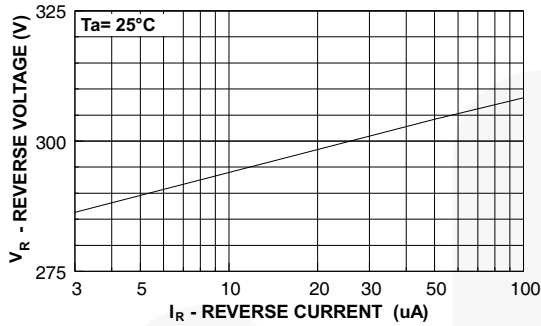


Figure 1. Reverse Voltage vs. Reverse Current
BV - 1.0 to 100 μ A

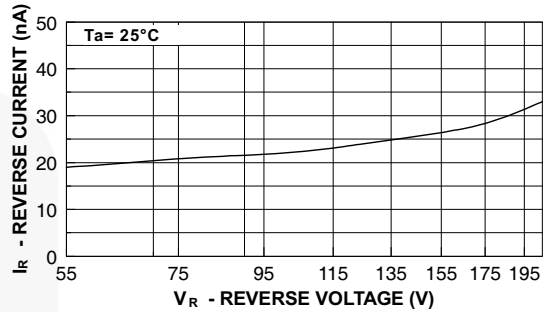


Figure 2. Reverse Current vs. Reverse Voltage
 I_R - 55 to 205 V

GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

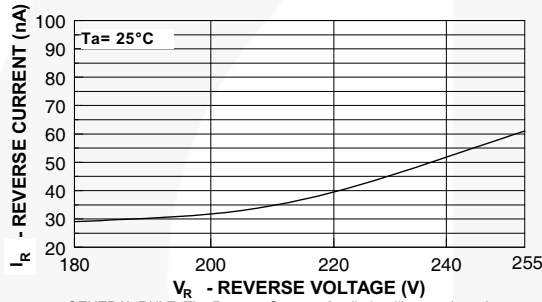


Figure 3. Reverse Current vs. Reverse Voltage
 I_R - 180 to 255 V

GENERAL RULE: The Reverse Current of a diode will approximately double for every ten Degree C increase in Temperature

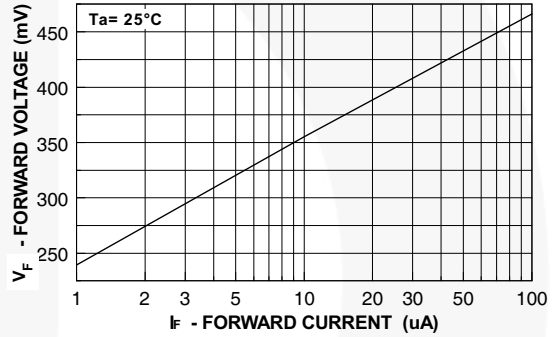


Figure 4. Forward Voltage vs. Forward Current
 V_F - 1.0 to 100 μ A

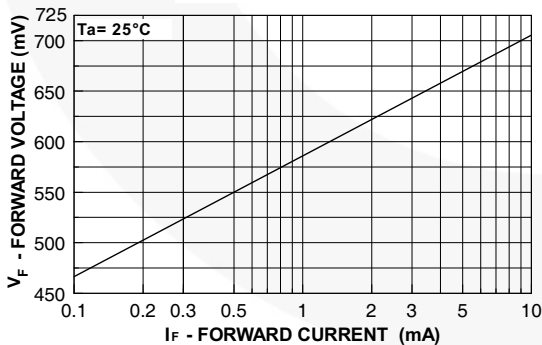


Figure 5. Forward Voltage vs. Forward Current
 V_F - 0.1 to 10 mA

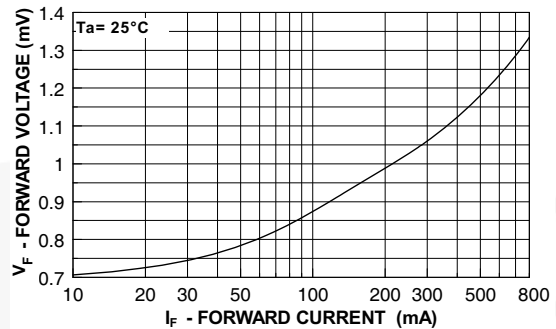


Figure 6. Forward Voltage vs. Forward Current
 V_F - 10 to 800 mA

Typical Performance Characteristics (Continued)

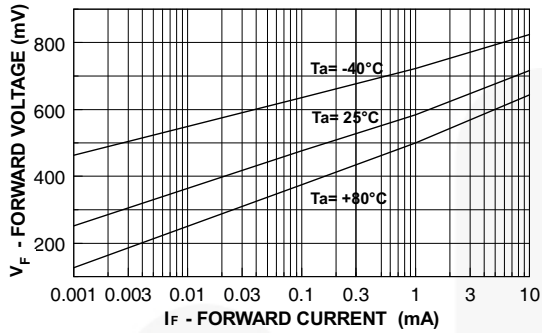


Figure 7. Forward Voltage vs. Ambient Temperature
 $V_F - 1.0 \mu A - 10 mA (-40 \text{ to } +80^\circ C)$

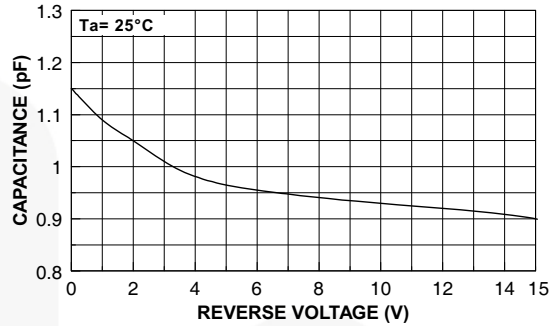


Figure 8. Capacitance vs. Reverse Voltage

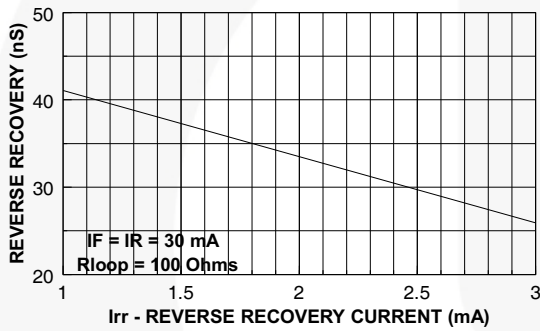


Figure 9. Reverse Recovery Time vs. Reverse Recovery Current (I_{rr})

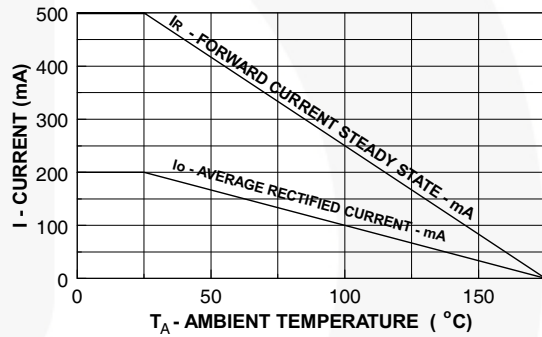


Figure 10. Average Rectified Current (I_O) and Forward Current (I_F) vs. Ambient Temperature (T_A)

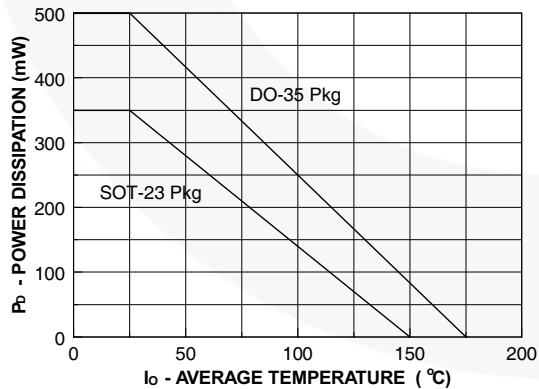


Figure 11. Power Derating Curve



LAND PATTERN
RECOMMENDATION



SEE DETAIL A



DETAIL A
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
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